Abstract

SEMICONDUCTOR DEVICE AND METHOD OF FORMING RDL WIDER THAN CONTACT PAD ALONG FIRST AXIS AND NARROWER THAN CONTACT PAD ALONG SECOND AXIS

A semiconductor device has a semiconductor die and first conductive layer formed over a surface of the semiconductor die. A first insulating layer is formed over the surface of the semiconductor die. A second insulating layer is formed over the first insulating layer and first conductive layer. An opening is formed in the second insulating layer over the first conductive layer. A second conductive layer is formed in the opening over the first conductive layer and second insulating layer. The second conductive layer has a width that is less than a width of the first conductive layer along a first axis. The second conductive layer has a width that is greater than a width of the first conductive layer along a second axis perpendicular to the first axis. A third insulating layer is formed over the second conductive layer and first insulating layer.

(Fig. 5c)